

# NPN & PNP General Purpose Amplifier

This complementary device is for use as a medium power amplifier and switch requiring collector currents up to 500 mA. Sourced from Process 19 and 63. See FFB2222A (NPN) and FFB2907A (PNP) for characteristics.

#### Absolute Maximum Ratings\* T<sub>4</sub> = 25°C unless otherwise noted

Symbol	Parameter	Value	Units	
V <sub>CEO</sub>	Collector-Emitter Voltage	30	V	
V <sub>CBO</sub>	Collector-Base Voltage	60	V	
V <sub>EBO</sub>	Emitter-Base Voltage	5.0	V	
lc	Collector Current - Continuous	500	mA	
T <sub>J</sub> , T <sub>stg</sub>	Operating and Storage Junction Temperature Range	-55 to +150	°C	

\*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

### NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.

2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.
3) All voltages (V) and currents (A) are negative polarity for PNP transistors.

## **Thermal Characteristics** $T_A = 25^{\circ}C$ unless otherwise noted

Symbol	Characteristic	Max Units		
		FFB2227A	FMB2227A	
PD	Total Device Dissipation	300	700	mW
	Derate above 25°C	2.4	5.6	mW/°C
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	415	180	°C/W

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# NPN & PNP General Purpose Amplifier (continued)

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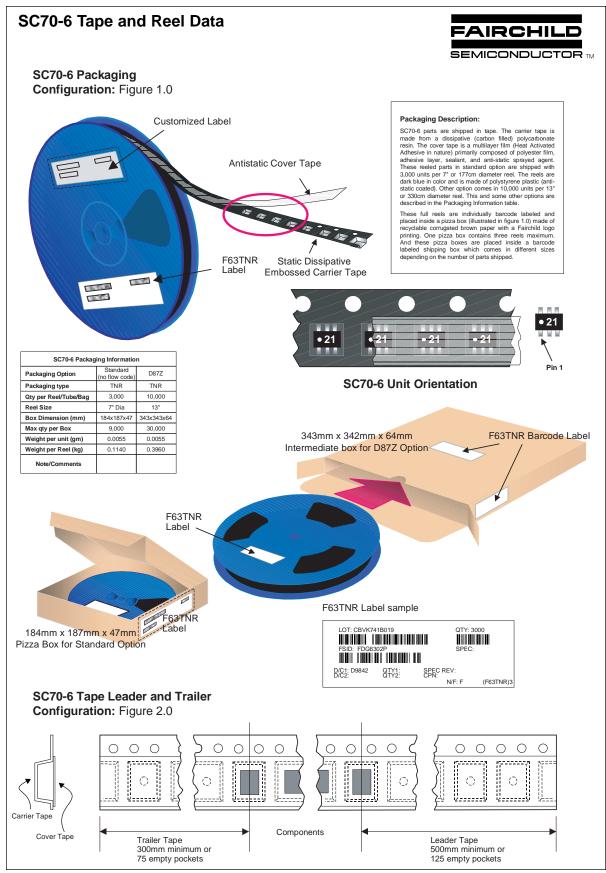
Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
OFF CHAP	RACTERISTICS					
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage*	$I_{\rm C} = 10 \text{ mA}, I_{\rm B} = 0$	30			V
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	$I_{C} = 10 \ \mu A, \ I_{E} = 0$	60			V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	$I_{E} = 10 \ \mu A, I_{C} = 0$	5.0			V
I <sub>CBO</sub>	Collector Cutoff Current	$V_{CB} = 50 \text{ V}, I_E = 0$			30	nA
I <sub>EBO</sub>	Emitter Cutoff Current	$V_{EB} = 3.0 \text{ V}, I_{C} = 0$			30	nA
h <sub>FE</sub>	DC Current Gain	$I_{C} = 1.0 \text{ mA}, V_{CE} = 10 \text{ V}$ $I_{C} = 10 \text{ mA}, V_{CE} = 10 \text{ V}$ $I_{C} = 150 \text{ mA}, V_{CE} = 10 \text{ V}^{*}$	50 75 100			
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage*	$\label{eq:lc} \begin{array}{l} I_{C} = 300 \text{mA}, \ V_{CE} = 10 \ \text{V}^{\star} \\ I_{C} = 150 \ \text{mA}, \ I_{B} = 15 \ \text{mA} \\ I_{C} = 300 \ \text{mA}, \ I_{B} = 30 \ \text{mA} \end{array}$	30		0.4	V V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage*	$I_{\rm C} = 150 \text{ mA}, I_{\rm B} = 15 \text{ mA}$			1.3	V
SMALL SI	GNAL CHARACTERISTICS Current Gain - Bandwidth Product	$I_{C} = 50 \text{ mA}, V_{CE} = 20 \text{ V},$ f = 100 MHz		250		MHz
C <sub>obo</sub>	Output Capacitance	$V_{CB} = 10 \text{ V}, \text{ I}_{E} = 0, \text{ f} = 100 \text{ kHz}$		4.0		pF
Cibo	Input Capacitance	V <sub>EB</sub> = 2.0 V, I <sub>C</sub> = 0, f = 100 kHz		12		pF
NF	Noise Figure	$I_{C}$ = 100 μA, V <sub>CE</sub> = 10 V, R <sub>S</sub> = 1.0 kΩ, f = 1.0 kHz		2.0		dB
SWITCHII	NG CHARACTERISTICS					
t <sub>on</sub>	Turn-on Time	$V_{CC} = 30 \text{ V}, \text{ I}_{C} = 150 \text{ mA},$		30		ns
t <sub>d</sub>	Delay Time	I <sub>B1</sub> = 15 mA		8.0		ns
tr	Rise Time	1		20		ns
t <sub>off</sub>	Turn-off Time	$V_{CC} = 6.0 \text{ V}, I_{C} = 150 \text{ mA}$	1	80		ns
ts	Storage Time	I <sub>B1</sub> = I <sub>B2</sub> = 15 mA		60		ns
		4			+	

**\***Pulse Test: Pulse Width  $\leq$  300  $\mu$ s, Duty Cycle  $\leq$  2.0%

Fall Time

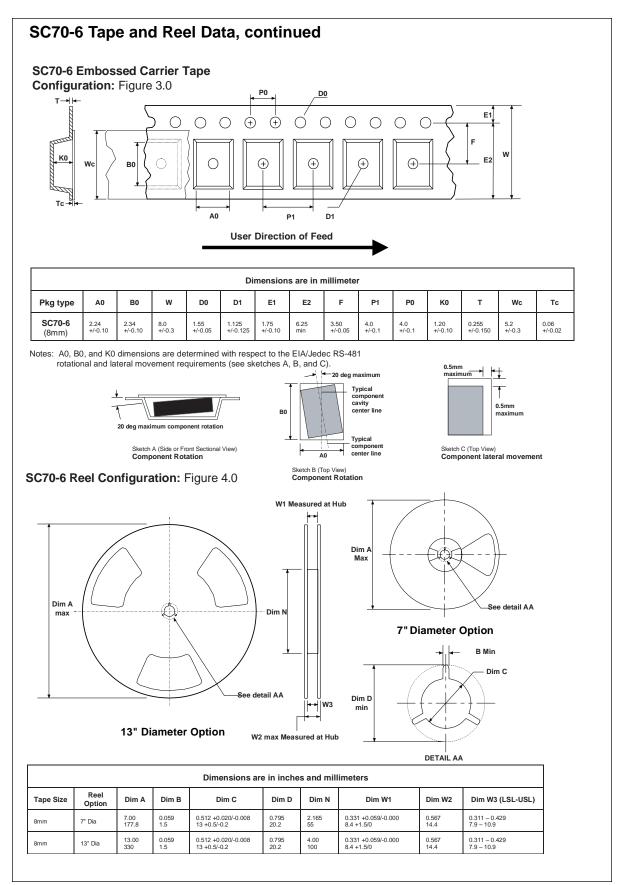
t<sub>f</sub>

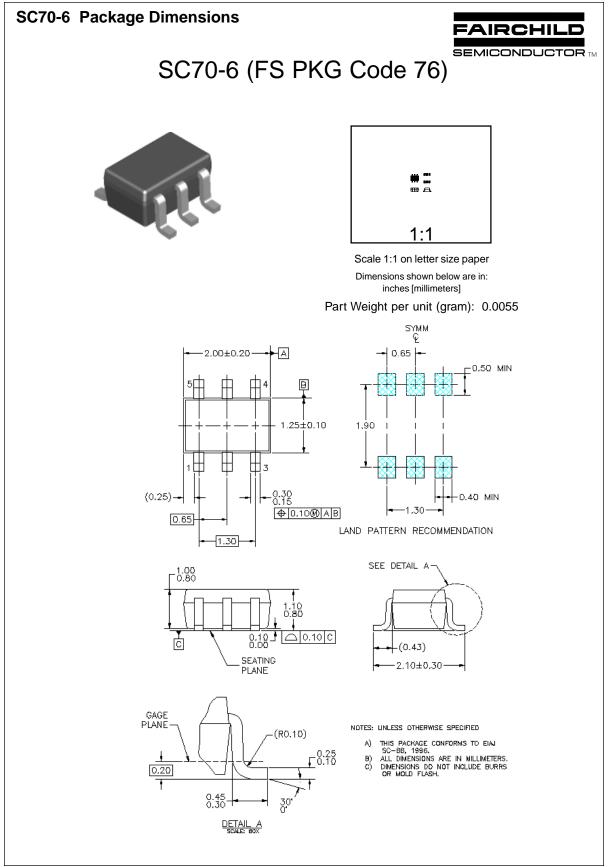
NOTE: All voltages (V) and currents (A) are negative polarity for PNP transistors.



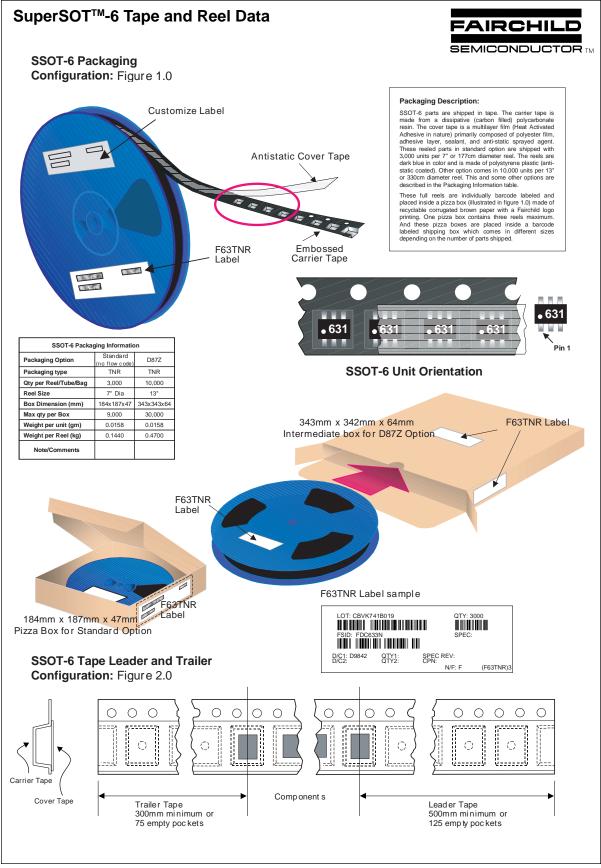
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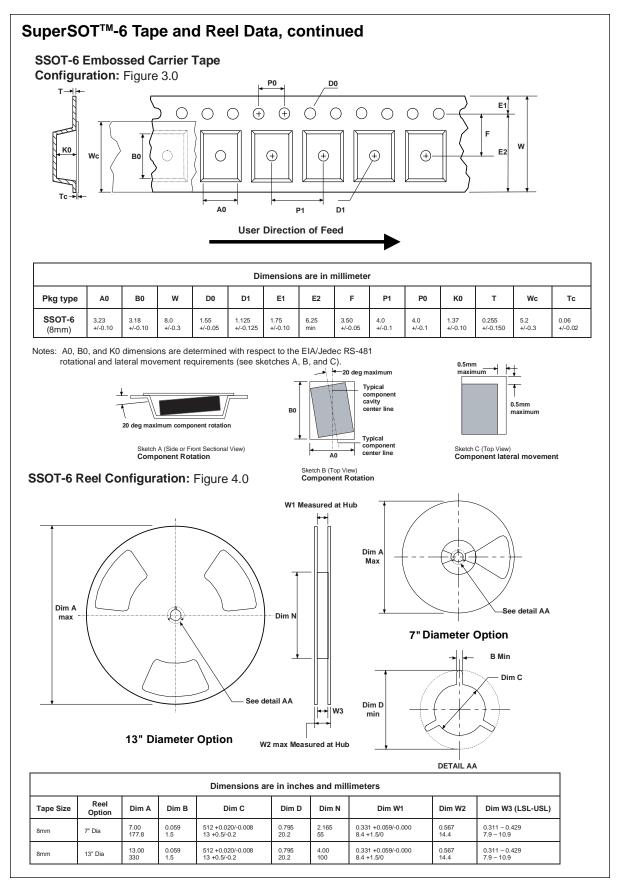


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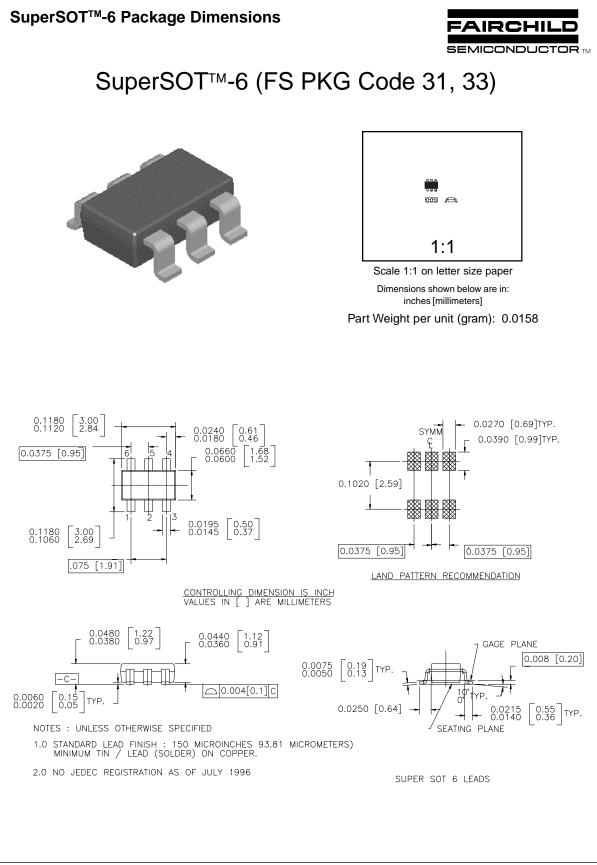


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